# Julian Stangl

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/6970144/publications.pdf

Version: 2024-02-01

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|---|---|---|---|
| 51 papers | 3,534 citations | 201575 27 h-index | 206029 48 g-index |
| 53 all docs | 53 docs citations | 53 times ranked | 6320 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Direct-bandgap emission from hexagonal Ge and SiGe alloys. Nature, 2020, 580, 205-209. | 13.7 | 231 |
| 2 | Micro-machining of PMN-PT Crystals with Ultrashort Laser Pulses. Applied Physics A: Materials Science and Processing, 2019, 125, 1. | 1.1 | 10 |
| 3 | Strain-tuning of the optical properties of semiconductor nanomaterials by integration onto piezoelectric actuators. Semiconductor Science and Technology, 2018, 33, 013001. | 1.0 | 58 |
| 4 | Self-Seeded Axio-Radial InAsâ€“InAs<sub>1â€“x</sub>P<sub>x</sub> Nanowire Heterostructures beyond â€œCommonâ€•VLS Growth. Nano Letters, 2018, 18, 144-151. | 4.5 | 15 |
| 5 | Quasi-epitaxial Metal-Halide Perovskite Ligand Shells on PbS Nanocrystals. ACS Nano, 2017, 11, 1246-1256. | 7.3 | 74 |
| 6 | Determining the directional strain shift coefficients for tensile Ge: a combined x-ray diffraction and Raman spectroscopy study. Measurement Science and Technology, 2017, 28, 025501. | 1.4 | 12 |
| 7 | Comparison of different bonding techniques for efficient strain transfer using piezoelectric actuators. Journal of Applied Physics, 2017, 121, 135303. | 1.1 | 13 |
| 8 | Cellular interfaces with hydrogen-bonded organic semiconductor hierarchical nanocrystals. Nature Communications, 2017, 8, 91. | 5.8 | 51 |
| 9 | Anodic oxide formation on aluminium-terbium alloys. Journal of Solid State Electrochemistry, 2016, 20, 1673-1681. | 1.2 | 14 |
| 10 | Evolution of thermal, structural, and optical properties of SiGe superlattices upon thermal treatment (Phys. Status Solidi A 3â•2016). Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 840-840. | 0.8 | 0 |
| 11 | Evolution of thermal, structural, and optical properties of SiGe superlattices upon thermal treatment. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 533-540. | 0.8 | 5 |
| 12 | Galvanic Exchange in Colloidal Metal/Metal-Oxide Core/Shell Nanocrystals. Journal of Physical Chemistry C, 2016, 120, 19848-19855. | 1.5 | 9 |
| 13 | Strain distribution in single, suspended germanium nanowires studied using nanofocused x-rays. Nanotechnology, 2016, 27, 055705. | 1.3 | 13 |
| 14 | Phase Transformation in Radially Merged Wurtzite GaAs Nanowires. Crystal Growth and Design, 2015, 15, 4795-4803. | 1.4 | 27 |
| 15 | Detection of X-ray photons by solution-processed lead halide perovskites. Nature Photonics, 2015, 9, 444-449. | 15.6 | 916 |
| 16 | Structural investigations of the Î±12Siâ€“Ge superstructure. Journal of Applied Crystallography, 2015, 48, 262-268. | 1.9 | 3 |
| 17 | Hexagonal Silicon Realized. Nano Letters, 2015, 15, 5855-5860. | 4.5 | 142 |
| 18 | X-ray diffraction strain analysis of a single axial InAs<sub>1â€“x</sub>P<sub>x</sub>nanowire segment. Journal of Synchrotron Radiation, 2015, 22, 59-66. | 1.0 | 8 |

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|---|---|---|---|
| 19 | Lattice-Matched InGaAsâ€“InAlAs Coreâ€“Shell Nanowires with Improved Luminescence and Photoresponse Properties. Nano Letters, 2015, 15, 3533-3540. | 4.5 | 46 |
| 20 | (Invited) The Thermoelectric Properties of Ge/SiGe Based Superlattices: from Materials to Energy Harvesting Modules. ECS Transactions, 2014, 64, 929-937. | 0.3 | 1 |
| 21 | Tuning the Localized Surface Plasmon Resonance in Cu<sub>2â€“x</sub>Se Nanocrystals by Postsynthetic Ligand Exchange. ACS Applied Materials & Interfaces, 2014, 6, 17770-17775. | 4.0 | 68 |
| 22 | Unraveling the Coreâ€“Shell Structure of Ligand-Capped Sn/SnOxNanoparticles by Surface-Enhanced Nuclear Magnetic Resonance, MÃ¶ssbauer, and X-ray Absorption Spectroscopies. ACS Nano, 2014, 8, 2639-2648. | 7.3 | 87 |
| 23 | Hydrogen-Bonded Organic Semiconductor Micro- And Nanocrystals: From Colloidal Syntheses to (Opto-)Electronic Devices. Journal of the American Chemical Society, 2014, 136, 16522-16532. | 6.6 | 75 |
| 24 | Gold-Free Ternary IIIâ€“V Antimonide Nanowire Arrays on Silicon: Twin-Free down to the First Bilayer. Nano Letters, 2014, 14, 326-332. | 4.5 | 88 |
| 25 | Au-Seeded Growth of Vertical and in-Plane IIIâ€“V Nanowires on Graphite Substrates. Nano Letters, 2014, 14, 1707-1713. | 4.5 | 41 |
| 26 | Scanning X-ray strain microscopy of inhomogeneously strained Ge micro-bridges. Journal of Synchrotron Radiation, 2014, 21, 111-118. | 1.0 | 37 |
| 27 | The benefit of the European User Community from transnational access to national radiation facilities. Journal of Synchrotron Radiation, 2014, 21, 638-639. | 1.0 | 2 |
| 28 | Ge/SiGe superlattices for thermoelectric energy conversion devices. Journal of Materials Science, 2013, 48, 2829-2835. | 1.7 | 23 |
| 29 | Tuning the Magnetic Properties of Metal Oxide Nanocrystal Heterostructures by Cation Exchange. Nano Letters, 2013, 13, 586-593. | 4.5 | 91 |
| 30 | Unit cell structure of the wurtzite phase of GaP nanowires: X-ray diffraction studies and density functional theory calculations. Physical Review B, 2013, 88, . | 1.1 | 28 |
| 31 | xrayutilities: a versatile tool for reciprocal space conversion of scattering data recorded with linear and area detectors. Journal of Applied Crystallography, 2013, 46, 1162-1170. | 1.9 | 100 |
| 32 | From Highly Monodisperse Indium and Indium Tin Colloidal Nanocrystals to Self-Assembled Indium Tin Oxide Nanoelectrodes. ACS Nano, 2012, 6, 4113-4121. | 7.3 | 48 |
| 33 | Crystal structure control in Au-free self-seeded InSb wire growth. Nanotechnology, 2011, 22, 145603. | 1.3 | 45 |
| 34 | X-ray Nanodiffraction on a Single SiGe Quantum Dot inside a Functioning Field-Effect Transistor. Nano Letters, 2011, 11, 2875-2880. | 4.5 | 65 |
| 35 | Unit Cell Structure of Crystal Polytypes in InAs and InSb Nanowires. Nano Letters, 2011, 11, 1483-1489. | 4.5 | 117 |
| 36 | Self-seeded, position-controlled InAs nanowire growth on Si: A growth parameter study. Journal of Crystal Growth, 2011, 334, 51-56. | 0.7 | 41 |

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|---|---|---|---|
| 37 | Strained MOSFETs on ordered SiGe dots. Solid-State Electronics, 2011, 65-66, 81-87. | 0.8 | 2 |
| 38 | Coreâ€“shell nanowires: From the ensemble to single-wire characterization. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 316-319. | 0.6 | 15 |
| 39 | Coherence and wavefront characterization of Si-111 monochromators using double-grating interferometry. Journal of Synchrotron Radiation, 2010, 17, 299-307. | 1.0 | 38 |
| 40 | Imaging the displacement field within epitaxial nanostructures by coherent diffraction: a feasibility study. New Journal of Physics, 2010, 12, 035006. | 1.2 | 25 |
| 41 | Growth Mechanism of Self-Catalyzed Group IIIâ^'V Nanowires. Nano Letters, 2010, 10, 4443-4449. | 4.5 | 177 |
| 42 | Determination of the wurtzite content and orientation distribution of nanowire ensembles. Materials Research Society Symposia Proceedings, 2009, 1206, 113901. | 0.1 | 0 |
| 43 | Spatially resolved strain within a single SiGe island investigated by Xâ€ray scanning microdiffraction. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1829-1832. | 0.8 | 12 |
| 44 | Structural Investigations of Coreâ^'shell Nanowires Using Grazing Incidence X-ray Diffraction. Nano Letters, 2009, 9, 1877-1882. | 4.5 | 47 |
| 45 | X-ray diffraction investigation of a three-dimensional Si/SiGe quantum dot crystal. Physical Review B, 2009, 79, . | 1.1 | 25 |
| 46 | Evidence of stacking-fault distribution along an InAs nanowire using micro-focused coherent X-ray diffraction. Journal of Applied Crystallography, 2008, 41, 272-280. | 1.9 | 27 |
| 47 | Three-Dimensional Si/Ge Quantum Dot Crystals. Nano Letters, 2007, 7, 3150-3156. | 4.5 | 175 |
| 48 | Au-Free Epitaxial Growth of InAs Nanowires. Nano Letters, 2006, 6, 1817-1821. | 4.5 | 207 |
| 49 | Colloidal HgTe Nanocrystals with Widely Tunable Narrow Band Gap Energies:Â From Telecommunications to Molecular Vibrations. Journal of the American Chemical Society, 2006, 128, 3516-3517. | 6.6 | 176 |
| 50 | Strain-compensated Si/Si0.2Ge0.8 quantum cascade structures grown on Si0.5Ge0.5 pseudo-substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 613-617. | 1.3 | 0 |
| 51 | High Resolution X-Ray Diffraction and Reflectivity Studies of Vertical and Lateral Ordering in Multiple Self-Organized InGaAs Quantum Dots. Japanese Journal of Applied Physics, 1997, 36, 4084-4087. | 0.8 | 4 |